

SHINDENGEN

Bridge Diode

Square In-line Package

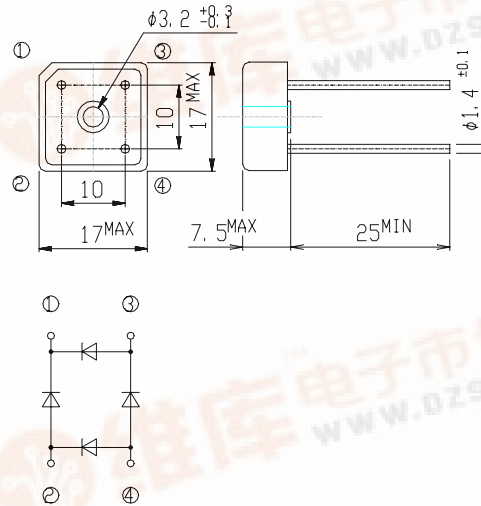
S4VB20

200V 4A

OUTLINE DIMENSIONS

Case : S4VB

Unit : mm



RATINGS

● Absolute Maximum Ratings

| Item | Symbol | Conditions | Ratings | Unit |
|-----------------------------------|------------------|--|---------|------------------|
| Storage Temperature | T _{stg} | | -40~150 | °C |
| Operating Junction Temperature | T _j | | 150 | °C |
| Maximum Reverse Voltage | V _{RM} | | 200 | V |
| Average Rectified Forward Current | I _O | 50Hz sine wave, R-load, Ta=40°C With heatsink θ _{fa} =10°C/W | 4 | A |
| | | 50Hz sine wave, R-load, Ta=40°C Without heatsink | 2.6 | |
| Peak Surge Forward Current | I _{FSM} | 50Hz sine wave, Non-repetitive 1cycle peak value, T _j =25°C | 80 | A |
| Current Squared Time | I ² t | 1ms ≤ t < 10ms T _c =25°C | 32 | A ² s |
| Mounting Torque | TOR | (Recommended torque : 0.5N·m) | 0.8 | N·m |

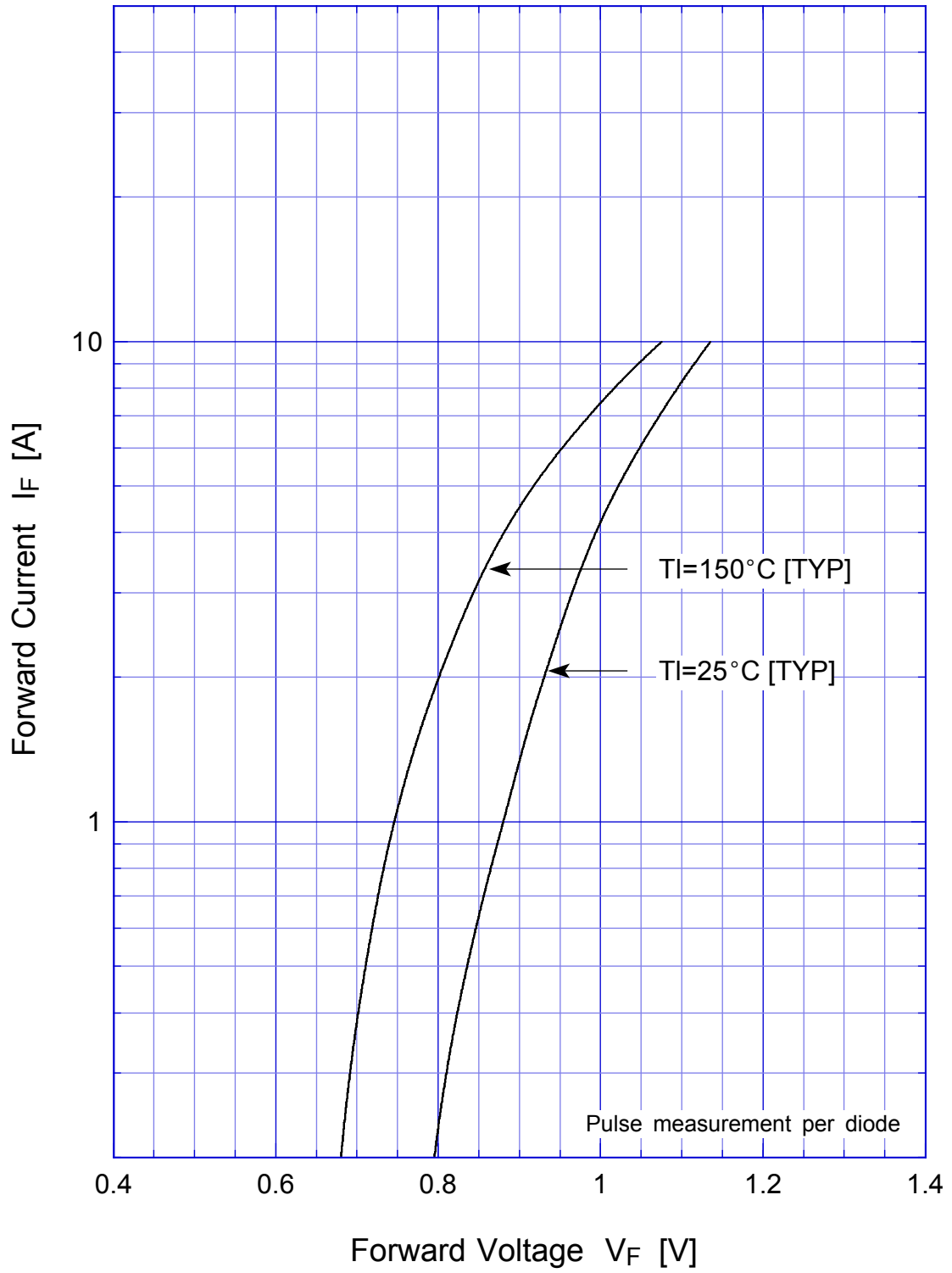
● Electrical Characteristics (T_i=25°C)

| Item | Symbol | Conditions | Ratings | Unit |
|--------------------|-----------------|--|----------|------|
| Forward Voltage | V _F | I _F =2A, Pulse measurement, Rating of per diode | Max.1.05 | V |
| Reverse Current | I _R | V _R =V _{RM} , Pulse measurement, Rating of per diode | Max.10 | μA |
| Thermal Resistance | θ _{jl} | junction to lead | Max.4.5 | °C/W |



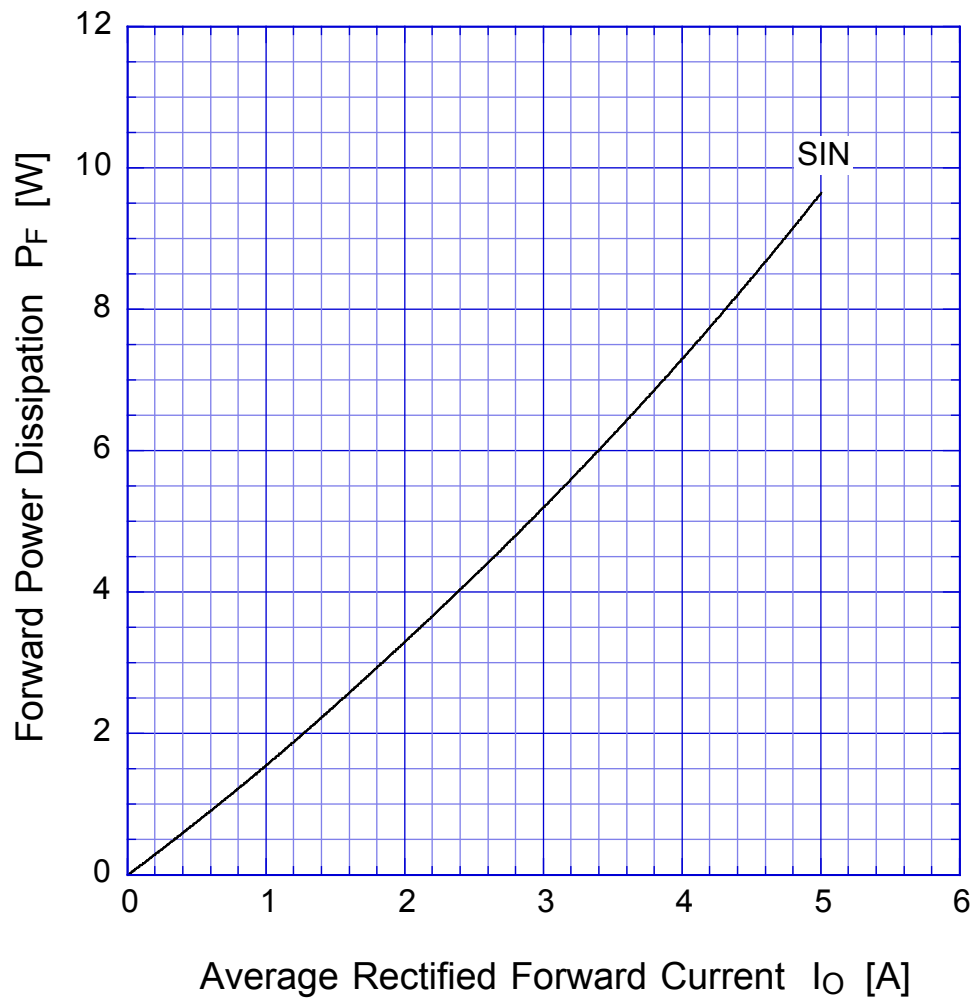
S4VBx

Forward Voltage



S4VBx

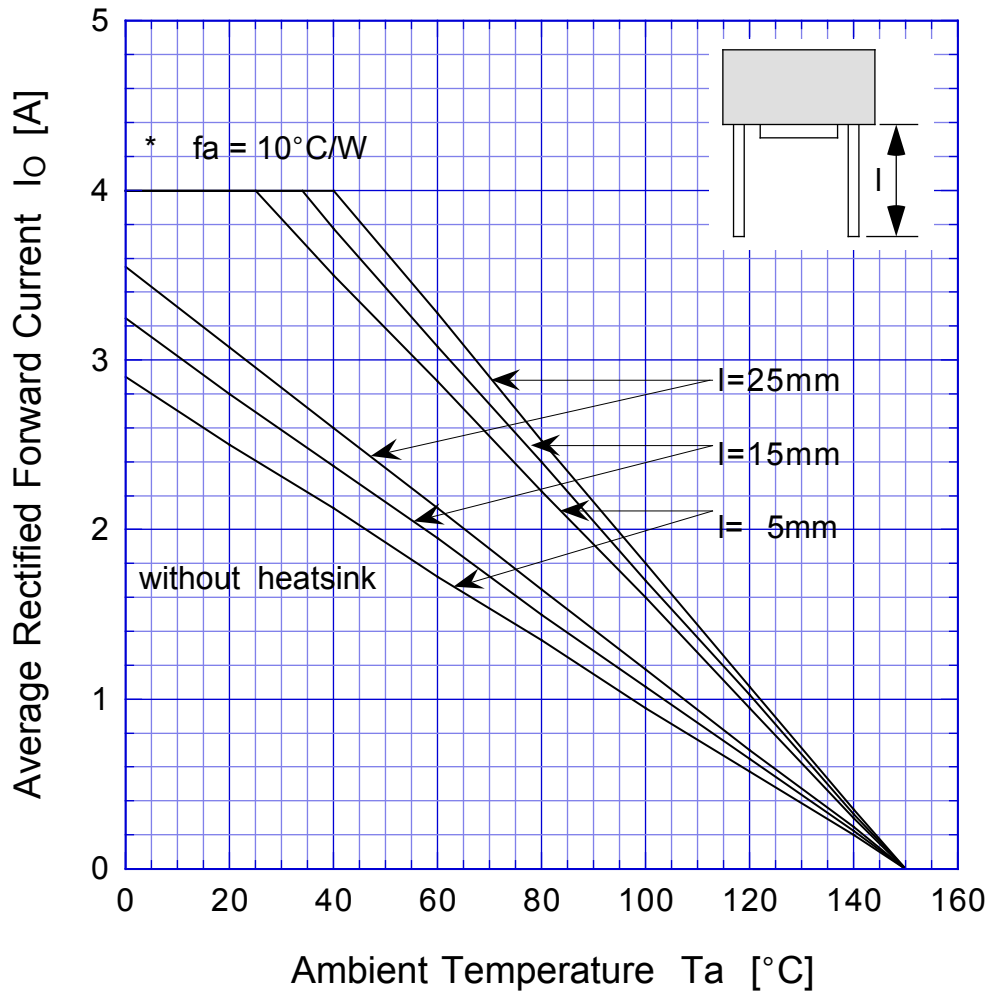
Forward Power Dissipation



$T_j = 150^\circ\text{C}$
Sine wave

S4VBx

Derating Curve



Sine wave

R-load

Free in air

* with thermal compound, TOR=3kg-cm

S4VBx

Peak Surge Forward Capability

